

Denton Discovery 18 SOP

Purpose and Scope

This document provides job breakdowns and references for the Denton Discovery 18 sputtering operations.

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Reference Documents

Reference Documents	Specification No.
NanoFab User Guide	HTTPS://WWW.NANOFAB.UTAH.EDU/DOCUMENTS/201 6/02/SMBB-USER-GUIDE.PDF/

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Acronyms, Abbreviations and Definitions

Term	Description	
SOP	Standard Operating Procedure	
JB	Job Breakdown	
JR	Job Reference	

Equipment and Supplies

Description	
Denton 18 Sputter System	
Wafer/Sample	
Target	
Allen Wrench	
Liquid Nitrogen Dewar	

Safety

Safety alert symbol



The Safety Alert Symbol is used in conjunction with signal words to convey a personal injury hazard is present.

Signal words

DANGER	Indicates an <u>imminently</u> hazardous situation, which if not avoided, will result in death or serious injury. The Safety Alert Symbol should always be used.
WARNING	Indicates a <u>potentially</u> hazardous situation, which if not avoided, may result in death or serious injury. If the safety alert symbol is NOT used in conjunction with this signal word, then the hazard conveyed is severe equipment or material damage.
CAUTION	Indicates a <u>potentially</u> hazardous situation, which if not avoided, may result in minor or moderate injury. If the safety alert symbol is NOT used in conjunction with this signal word, then the hazard conveyed is minor equipment or material damage.

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Forms

Training Form

Trainee						
Area:						
This pe	rson has been declared qualified to tra	in others 🗌 (che	ck if "Yes	")		
Item #	Task			Date Train Completed	ing	Trainer
1	Know the safety hazards of the tool					
2	Enable & Disable tool using HSC					
3	Know and agree to use HSC data comeasurement samples.	llections, generat	e			
4	Demonstrate venting and pumping n	nain chamber.				
5	Correctly remove and install targets, types and details associated with inst	know the different tallation/deinstal	ent ation.			
6	Use the correct tools, tray, resistance check, adjustment tools, etc.					
7	Know the conditions of the auto enable button, on vs. off.					
8	Demonstrate gas flow set up					
9	Demonstrate power set up					
10	Demonstrate plasma ignition, pre sputter and deposition.					
11	Demonstrate post deposition activities including locking and measuring samples.					
Trainin	g Notes (Optional)					
Run con	Run completion dates: 1) 2) 3) 4) 5)					
		·				· ·



JB1 – Enable/Disable the Denton 18 (1 of 1)

1.	A. Log into HSC and navigate to the NanoFab Deposition dropdown.	 twensity of Utah Core Lats resource.cores.utah.edu/auth/login University of Utah Core Labs Login Username Patavord (required) Pasavord @ Login	
2.	A. Select the Denton 18 Sputter.B. Select the desired block of time.	Deposition (14) ALD - Cambridge Figi F200 (Bay G - Jim) E-Beam - Denton S200 (Bay F - Jim) O MCCVD - Agnitron Imperium [2006N - Kathy] MCCVD - Agnitron Imperium [2006N - Kathy] Parylene Coater (2227 - Kathy] Sporter - Denton 635 (Au, Ce A, TD [Bay F - Joe] Sporter - Denton Discovery H3 [Bay F - Joe] Sporter - TMV Super [Bay F - Joe]	
3.	A. Send "Unlock" to the tool for starting.B. Send "Lock" command for stopping.	Owner Jim Pierce Charge Account Nanofab Cleanroom Maintenance DL Dummy C Scheduled Notification I5m A dd Notification Interlock Controls Process (required) Deposition Deposition	

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JB2 – Venting the Main Chamber (1 of 1)



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JB3 – Removing and/or Installing Targets (1 of 3)

Note: If your sputtering target of choice is already installed. The target doesn't need to be removed or installed. Follow the appropriate Remove or Install steps for your conditions.

Remove Old Target:

The seal can be damaged by twisting or rocking the sputter head aggressively. Be careful to gently remove the dark shield with enough force to remove, but not damage the feedthrough seal. Be careful of pinch points and sharp objects.

- A. Place the catch tray into the bottom of the sputter.
- B. Use an Allen wrench to loosen screws a couple of turns on both sides of the clamp. Place the shutter and all vacuum components on a clean sheet of aluminum foil.
- C. Use the wing nut to carefully loosen and remove the dark shield.
- D. Use an Allen wrench to remove the screws from the target clamp and remove the old target.
- E. Place the old target in its corresponding bag and put it on the sputtering target shelf. The target bags for the tool are displayed on the side of the tool with respect to the appropriate cathode.



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JB3 – Removing and/or Installing Targets (2 of 3)

Note: If your sputtering target of choice is already installed, the target doesn't need to be installed.

Install New Target:

F. Insert new target into desired cathode for DC or RF sputtering. Only cathodes 1 and 2 have RF power supplied. All cathodes have DC power supplied.

Note: Make sure the smooth, flat side of the target is facing toward the sputter head so good heat conduction occurs. The eroded (used) circular pattern should be facing out.

- G. Put the target clamp over the new target in the sputter head and replace the screws and tighten them using the Allen wrench.
- H. Put the new target's bag in the corresponding pouch on the side of the rack. The sputter head's number is located outside the chamber where the water and electrical contacts are made.
- I. Replace the dark shield and tighten the three screws being careful not to over-tighten.
- J. Do a resistance test by placing one of the leads on the dark shield and placing the other lead on the target clamp ring. The resistance should read around 1 MegaOhm. If it is less than 100 kOhm, the target and the dark shield may be shorted. You should remove and then reinstall the dark shield with a larger gap between it and the target until the resistance is around 1 MegaOhm.



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JB3 – Removing and/or Installing Targets Continued (3 of 3)

- K. Replace the shutter and open and close it a few times (SHUTTER button on the control panel) to ensure it completely covers the target when the shutter is closed.
- L. To test the shutter, make sure the AUTO ENABLE light is not blinking.
- M. Press the SHUTTER button corresponding to the cathode number to open/close it.
- N. Test the open and close shutter buttons making sure there is no drag between the shutter and the dark shield. The gap between the shutter and dark shield should be no larger than a ¹/₄ inch.
- **3.** O. When testing is complete, close the shutter.
 - P. Repeat JB3 for any other new targets you want to install.
 - Q. Remove the catch tray when target installations are completed
 - R. If the inside of the machine is dirty, vacuum it.
 - S. Clean around the machine to remove dust that could harm your work.



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JB4 – Loading Samples (1 of 1)

A. Place the 6" sample holder in the round groove in the center of the main chamber. B. Place your clean, dry samples on the 6" sample holder. C. Test the sample rotation by pressing the ROTATION POWER button (AUTO ENABLE light must be off). A & B D. Turn off the ROTATION POWER after testing it. 1. HiVac Valve Gas#1 02/N2



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JB5 – Pumping Down Main Chamber (1 of 1)

- A. Check the Cryopump monitor. If it is greater than 20 degrees Kelvin do not continue, contact staff.
- B. Ensure the turbo controller is on and the light is green, if not, contacts staff.
- C. Close the lid to the main chamber and latch it in place.

Be careful of pinch points when closing the lid. The latch will open once under vacuum. Do not close it under vacuum.

- D. Make sure the AUTO ENABLE light is blinking. If not, press the AUTO ENABLE button.
- E. Press the CHAMBER AUTOPUMP button. The system will automatically rough down the chamber and open the Hi-Vac valve and Gate Valve. The ion gauge will come on automatically once conditions are met.
- F. Ensure the TC and IG pressures are displaying before leaving the tool. This process can take up to 15 minutes, but will take longer to achieve the desired base pressure.
- G. Prepare to gather required HSC data collections.
- H. Choose the desired sputtering method (DC or RF) and proceed to the appropriate JB6 6 for DC and JB7 for RF.



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JB6 – DC Sputtering Procedures (1 of 5)

Note:

- For best results wait until the base pressure (ion gauge green pressure readout) reads at less than 2 x 10 ^-6 Torr before sputtering. Higher pressures may oxidize metallic films.
- *The base pressure and the pump down time to be recorded in HSC at disable.*
- The red pressure readout meter should be zeroed once the process pressure is reached. To zero the readout hold the 'zero' button down for 3 seconds.

Start Argon Flow

- **1.** A. Turn off the AUTO ENABLE button, so it is not blinking.
 - B. Set argon gas flow rate to 40% by holding the #3 toggle switch in the SET PT. position and turning the adjustment screw to the right of the toggle switch.
 - *NOTE: The MFC is rated at 200 SCCM so a set point of 40% would be a flow rate of 80 SCCM.*
 - C. Turn on the Argon FLOW CONTROL toggle switch on the flow control panel.
 - D. Press the GAS 2 button on the touchscreen to start the argon flow.
 - *NOTE: The pressure readout on the red pressure readout meter and the green ion gauge should go up.*



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JB6 – DC Sputtering Procedures (2 of 5)

- E. Select desired sputter target material by pressing the SPUTTER HEAD SELECT button to toggle through the three different heads.
- F. Turn on the MDX 1.5 K power supply.
- G. Press the SET PT button and rotate the LEVEL knob to select the desired sputter power.
- H. Turn on the ROTATION POWER button to start the samples rotating for more uniform sputter thickness.



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JB6 – DC Sputtering Procedures (3 of 5)

Pre-sputter

3.

- I. Ignite the plasma by pressing the OUTPUT ON button.
- J. Press the RIGHT DISPLAY ACTUAL button a few times to toggle through the power, voltage, and current, to make sure you are sputtering with the right power settings.
- K. If the voltage is high (approx 1200 V), this means that the plasma did not ignite. Do the following:
 - a. Open the appropriate shutter then quickly close the shutter.
 - b. If the voltage drops, the plasma ignited, continue pre-sputter, if not press OUTPUT OFF and contact lab staff.

Allow the target to sputter with the shutter closed for about a minute to clean any oxides or absorbed contaminants off the surface of the target.



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JB6 – DC Sputtering Procedures (4 of 5)

DC Sputter

- L. Note the deposition pressure, time, power, and other parameters for HSC data collections. After deposition, please note the measured thickness and sheet resistance of the material.
- M. Open the shutter by pressing the SHUTTER # button that corresponds to the target you are sputtering from.
- N. Let the system run for the desired sputter deposition time. There is no automatic timer to shut off the system.
 - O. Press the OUTPUT OFF button on the MDX power supply when the deposition time is reached.
 - P. Close the shutter by pressing the SHUTTER number button that corresponds to the target you have been sputtering.
 - Q. If another material is to be deposited on top of the current sample, follow the appropriate Job Breakdown.



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JB6 – DC Sputtering Procedures (5 of 5)

<u>Shutdown</u>

5.

- R. Turn off the MDX 1.5 K power supply.
- S. Turn off Rotation Power.
- T. Turn off Argon flow.
- U. Turn off Gas 2.
- V. Toggle through Sputter Head Select until none of them are selected.



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JB7 – RF Sputtering Procedures (1 of 3)

Set up RF Sputter Parameters

- A. Turn on the RF power supply and tuning power supply that corresponds to the target you are going to sputter from (either cathode 1 or cathode 2).
- B. Press the SET PT button and rotate the LEVEL knob to select the desired sputter power.
- C. Turn on the ROTATION POWER button to start the samples rotating for more uniform sputter thickness.

Pre-sputter

- D. Ignite the plasma by pressing the RF ON button on the RF power supply. The tuning power supply will show if the plasma has ignited. If not, press the HI VAC valve to close it and allow the Argon pressure to build in the chamber. The plasma should ignite at about 110 mTorr (0.11 Torr) on the TC1 display. Press the HI VAC valve again to open it and allow the pressure to stabilize at the desired sputter pressure. DO NOT allow the TC1 pressure to exceed 140 mTorr or you will not be able to open the HI VAC valve until you do chamber autopump.
 - E. Allow the target to sputter with the shutter closed for about a minute to clean any absorbed contaminants off the surface of the target.



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JB7 – RF Sputtering Procedures (2 of 3)

RF Sputter

- F. Note the deposition pressure, time, power, and other parameters for the HSC data collection form. After deposition, please note the measured thickness and sheet resistance of the material you sputtered.
- G. Begin sputtering on your samples by opening the shutter by pressing the SHUTTER # button that corresponds to the target you are sputtering from. Make sure the light turns on.
- 2. H. Let the system run for the desired sputter deposition time. There is no automatic timer to shut off the system.
 - I. Press the RF OFF button on the RF power supply when the deposition time is reached.
 - J. Close the shutter by pressing the SHUTTER # button that corresponds to the target you have been sputtering.

If another material is to be deposited on top of the current samples, follow the appropriate Job Breakdown for DC or RF sputtering



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JB7 – RF Sputtering Procedures (3 of 3)





JB8 – Unloading Samples (1 of 1)

A. Vent Main Chamber refer to JB2 B. Remove your samples and return the holder to the sputter tool. А Pump down the sputter tool refer to JB5. C. D. Lock the tool in HSC refer to JB1. E. Enter your run data and lock the Denton Discovery 18 Sputter system in С Backing Valve Mech Turbo Pump HiVac Valve HSC. Gas#2 Ar Shutter Shutter Gas#1 02/N2 Sample Sample Holder IN Holder OUT Rotation Power В

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JR1 – HSC Data Collection (1 of 3)

Denton Disc 18 Data Entry Form		
Submitting on behalf of		
Jim Pierce Q		
Save form for later Load saved form		
Substrate [Required]		Other Substrate
Please Select A Value 💠		
Select the type of substrate loaded onto the chuck.		Describe the non-standard substrate.
Changed a Target? [Required]		
○ Yes		
O No		
Has any target been changed?		
Number of Repeat Runs	Cryo Temp (°K) [Required - No Value Se	et]
<u>^</u>	×	
Enter the number of times this exact process (with identical parameters) has been repeated. [1 to Any]	Enter the value of the Cryo temperature in °C [A	ny to Any]
Base Pressure [Required - No Value Set]	Base Pressure Unit [Required]	
×	O 10E-6	
Enter the numeric value for the Base Pressure [Any to Any]	() 10E-7	
	Select the unit recorded for the Base Pressure.	
Sputter Material 1 Parameters		
Layer 1 Material [Required]	Other Targe	et Material
Please Select A Value 💠		
Select the material of the Target used.	Describe the n	non-standard target used for the sputtered film.
Power Supply [Required]		
○ DC		
O RF1		
RF2 Select the Bours Supply used for this posterial		
Select the Power Supply used for this material.		
Pre-Sputter Time (min) [Required - No Value Set] Sput	tter Time (min) [Required - No Value Set]	Sputter Power (W) [Required - No Value Set]
	∧ ▼	
Enter the Pre-Sputter time in minutes [Any to Any] Enter	the time the material was sputtered in minutes [Any to A	[Any] Enter the power used to sputter the material in Watts [Any to Any]
Argon Sputter Pressure (mTorr) [Required - No Value Set] Argo	on Flow (%) [Required - No Value Set]	Oxygen Flow (%)
×	×	× ×
Enter the pressure of the Argon Sputter in mTorr [Any to Any] Enter	the Argon Flow in percent. [Any to Any]	Enter the Oxygen flow in percent. [Any to Any]
Material 1 Precious Metal larget Use		
If a precious metal target was used for this material, select it below and enter the	e applicable data to assign the appropriate charg	jes.
ladium		
Palladium		
Platinum		

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Palladium Platinum

JR1 – HSC Data Collection (2 of 3)

Sputter Material 2 Parameters		
Layer 2 Material [Required]	Other Target Material	
Please Select A Value 🔶		
Select the material of the Target used.	Describe the non-standard	target used for the sputtered film.
Pre-Sputter Time (min)	Sputter Time (min)	Sputter Power (W)
Enter the Pre-Sputter time in minutes [Any to Any]	Enter the time the material was sputtered in minutes [Any to Any]	Enter the power used to sputter the material in Watts [Any to Any]
Argon Sputter Pressure (mTorr)	Argon Flow (%)	Oxygen Flow (%)
× •	× · · ·	
Enter the pressure of the Argon Sputter in mTorr [Any to Any]	Enter the Argon Flow in percent. [Any to Any]	Enter the Oxygen flow in percent. [Any to Any]
Material 2 Precious Metal Target Use		
If a precious metal target was used for this material, select it bel	ow and enter the applicable data to assign the appropriate charges.	
Gold		
Indium		
Palladium		
Platinum		
Sputter Material 3 Parameters		
Layer 3 Material [Required]	Other Target Material	
Please Select A Value 🛊		
Select the material of the Target used.	Describe the non-standard	target used for the sputtered film.
Pre-Sputter Time (min)	Sputter Time (min)	Sputter Power (W)
× •	<u>^</u>	
Enter the Pre-Sputter time in minutes [Any to Any]	Enter the time the material was sputtered in minutes [Any to Any]	Enter the power used to sputter the material in Watts [Any to Any]
Argon Sputter Pressure (mTorr)	Argon Flow (%)	Oxygen Flow (%)
<u>^</u>	<u>^</u>	<u>^</u>
Enter the pressure of the Argon Sputter in mTorr [Any to Any]	Enter the Argon Flow in percent. [Any to Any]	Enter the Oxygen flow in percent. [Any to Any]
Material 3 Precious Metal Target Use		
If a precious metal target was used for this material, select it be	low and enter the applicable data to assign the appropriate charges.	
Gold		
Indium		

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JR1 – HSC Data Collection (3 of 3)

Measurement Results		
Measurement Sites 1 T 2 3 4 5 B Film Thickness Unit Angstrom (Å) Nanometer (mm) Micron (µm)		
Select the unit for the Measured Thickness Value Film Thickness, Site 1 Enter the measured value of the thickness for site 1 (Any to Any) Film Thickness, Site 2	Sheet Resistance, Site 1 (ohm/sq)	Film Stress (MPa)
Film Thickness, Site 3 Film Thickness, Site 4 Film Thickness, Site 4	Sheet Resistance, Site 3 (ohm/sq) Finter the measured value of the Sheet Resistance for Site 3 (in ohm/sq) (Any to Any) Sheet Resistance, Site 4 (ohm/sq)	
Enter the measured value of the thickness for site 4 [Any to Any] Film Thickness, Site 5	Enter the measured value of the Sheet Resistance for Site 4 (in ohm/sq) [Any to Any] Sheet Resistance, Site 5 (ohm/sq)	
Enter the measured value of the thickness for site 5 [Any to Any]	Enter the measured value of the Sheet Resistance for Site S (in ohm/sq) (Any to Any)	
Measurement Comment		
Staff Support		
Staff Support Click HERE to enter charges for Staff Support. Onvalid/Missing Fields) Save form for later Load saved form		

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Typical Film Characteristics

Add Liquid Nitrogen

- A. Fill dewar with LN2 from the tank by the Oxford 100.
- B. Carry dewar back to clean room and slowly pour LN2 into metal funnel until 1/3 full. Funnel is on the back of the Denton sputter machine. See **Error! Reference source not found.**.
- C. Continue to add LN2 as needed.





Revision History

Rev	Author	Date	Description of Change
F	Jim Pierce	09 Sept 2024	Update SOP format, added Training Form for training.
Е	Kevin Hensley	29 Nov 2011	Ion gauge procedure, MFC change, and pressure readout
D	Kevin Hensley	04 Aug 2011	Changed gate valve instructions
С	Sam Bell	12 Jul 2011	Added instructions for cryopump and new touchscreen
В	Sam Bell	15 Apr 2011	Deleted load lock instructions
А	Sam Bell	19 Jan 2010	Initial